GeSe-embedded metal-oxide double heterojunctions for facilitating self-biased and efficient NIR photodetection.

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Supporting Information

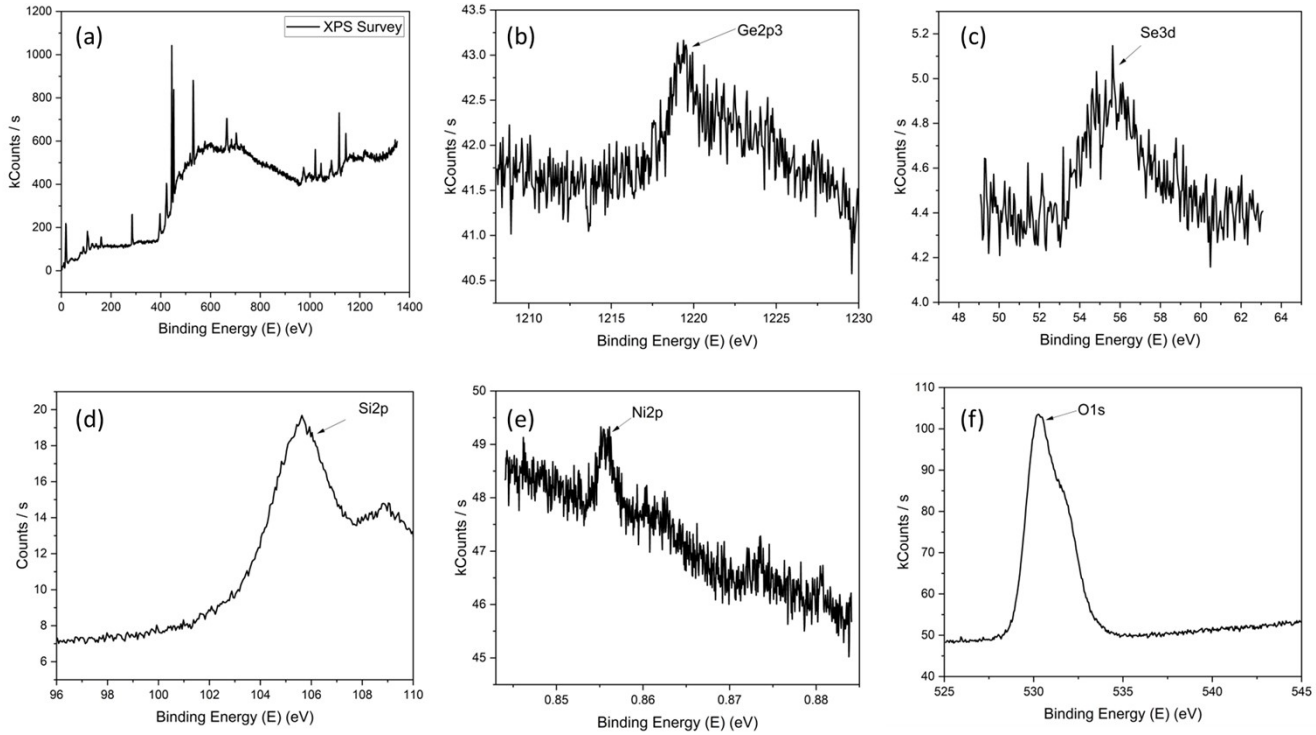

Figure S1. (a-h) X-ray photoelectron spectroscopy (XPS; PHI 5000 Versa Probe) under Al Kα at 25 W and 6.7×10^{-8} Pa was used to confirm the chemical composition and binding energy of the NiO and GeSe film on Si.

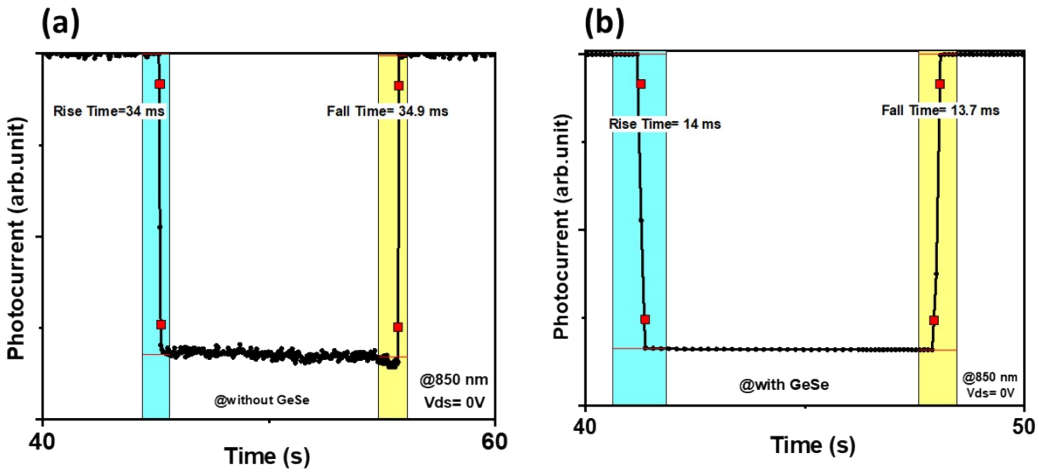

Figure S2: Response speed of the devices: (a) without GeSe interlayer and (b) with GeSe layer